

Features:

- Phototransistor output
- High sensitivity
- · Low-cost plastic housing
- Available with lenses for dust protection and ambient light filtration
- · Focused for maximum sensitivity



Description:

The **OPB703**, **OPB704** and **OPB705** consist of an Infrared (890nm) Light Emitting Diode (LED) and a NPN silicon Phototransistor, mounted side-by-side on converging optical axes in a black plastic housing and are designed for PCBoard mounting. The **OPB703WZ**, **OPB704WZ**, **OPB705WZ** and **OPB70BWZ** are designed for remote mounting utilizing interconnect wires of UL approved 26 AWG, 24" (61.0cm) minimum length, stripped and tinned.

The **OPB70AWZ** consists of an Infrared (890nm) Light Emitting Diode (LED) and a NPN silicon Photodarlington, mounted side-by-side on converging optical axes in a black plastic housing and is designed for remote mounting utilizing interconnect wires of UL approved 26 AWG, 24" (61.0cm) minimum length, stripped and tinned.

The **OPB70CWZ through OPB70FWZ** consist of a Visible (Red 640nm) Light Emitting Diode (LED) and a NPN silicon Phototransistor or Rbe Phototransistor, mounted side-by-side on converging optical axes in a black plastic housing and are designed for remote mounting utilizing interconnect wires of UL approved 26 AWG, 24" (61.0cm) minimum length, stripped and tinned.

Various lens options are available: No lens for the (OPB703, OPB703WZ), blue window for dust protection for the (OPB704, OPB704WZ, OPB70BWZ) and aperture lens for improved resolution for the (OPB705, OPB705WZ, OPB70AWZ, OPB70CWZ and OPB70DWZ). The OPB704G and OPB704GWZ offers excellent protection for dirty environments.

The phototransistor responds to illumination from the emitter when a reflective object passes within the field of view centered typically at 0.15" (3.8 mm).

Custom electrical, wire, cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact reflective object sensor
- · Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor
- Mark Detection
- Office Equipment
- Gaming Equipment

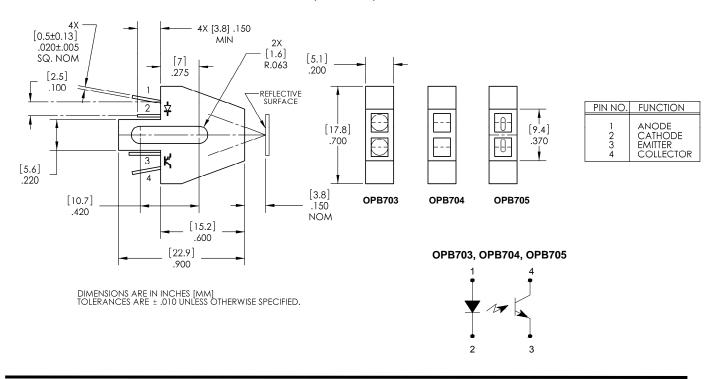
Ordering Information										
Part	LED Peak	Detector	Optical Cover	Lead or Wire						
OPB703				0.160" Leads						
OPB703WZ			None	24" / 26 AWG Wire						
OPB704				0.160" Leads						
OPB704WZ		Transistor	Blue	24" / 26 AWG Wire						
OPB704G	890 nm	Hallsistor	Window	0.160" Leads						
OPB704GWZ	090 11111			24" / 26 AWG Wire						
OPB705				0.160" Leads						
OPB705WZ			Aperture							
OPB70AWZ		Darlington								
OPB70BWZ		Rbe Transistor	Blue Window							
OPB70CWZ		Rbe Transistor	Aperture	24" / 26 AWG Wire						
OPB70DWZ	640 nm	Transistor	Aperture							
OPB70EWZ			Clear Window							
OPB70FWZ		Transistor	Cical William							



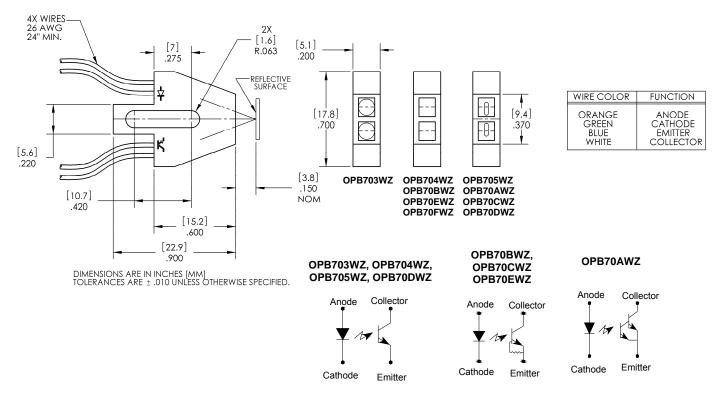
RoHS



OPB703, OPB704, OPB705

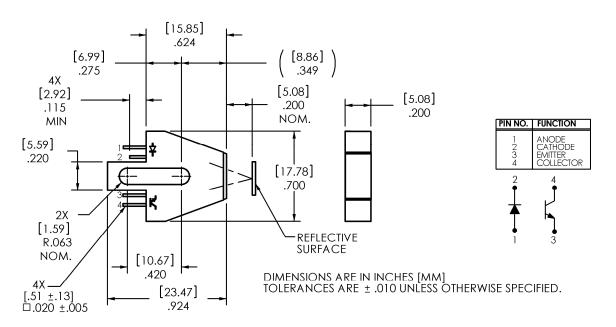


OPB703WZ, OPB704WZ, OPB705WZ, OPB70AWZ, OPB70BWZ, OPB70CWZ, OPB70DWZ

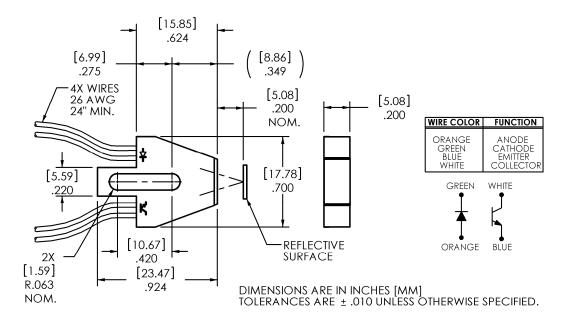




OPB704G



OPB704GWZ





Absolute Maximum Ratings	(T _A =25°C unless otherwise noted)
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St	torage Temperature Range	-40°C to +80° C
Le	ead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron]	240° C ⁽¹⁾

Input Diode

Forward DC Current	40 mA
Reverse DC Voltage	2 V
Power Dissipation	100 mW ⁽²⁾

Output Photodetector

Collector-Emitter Voltage Phototransistor Photodarlington	30 V 15 V
Emitter-Collector Voltage	5 V
Collector DC Current	25 mA
Power Dissipation	100 mW ⁽²⁾

Electrical Characteristics (T_A = 25° C unless otherwise noted)

(OPB703, OPB703WZ, OPB704, OPB704WZ, OPB705, OPB705WZ, OPB704G, OPB704GWZ)

SYMBOL	PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS
nput Diode	(See OP265 for additional information — for	reference	only)	•		
V_{F}	Forward Voltage	-	-	1.7	V	I _F = 40mA
I _R	Reverse Current		-	100	μΑ	V _R = 2 V
Output Pho	totransistor (See OP505 for additional inform	nation — f	or refere	nce only)	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30	-	-	V	I _{CE} = 100 μA
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	I _{EC} = 100μA
I _{CEO}	Collector Dark Current	-	-	250	nA	V _{CE} = 10 V, I _F = 0, E _E =0
Coupled						
I _{C(ON)}	On-State Collector Current OPB703, OPB703WZ OPB704, OPB704WZ OPB705, OPB705WZ	0.30 0.20 0.15		2.5 2.5 1.0	mA	$V_{CE} = 5 \text{ V}, I_F = 40 \text{mA}, d = 0.15$ " (3)(1)
	OPB704G, OPB704GWZ	0.50	-	6.0		$V_{CE} = 5 \text{ V}, I_F = 40 \text{mA}, \lambda = 0.20^{\circ} (3)(1)$

Notes:

 I_{CX}

Crosstalk

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) For OPB703, OPB704 and OPB705, derate linearly 1.67 mW/° C above 25° C.
- (3) For OPB703WZ, OPB704WZ, OPB705WZ, OPB70BWZ, OPB704G and OPB704GWZ derate linearly 1.82 mW/° C above 25° C.

20

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μΑ

- (4) The distance from the assembly face to the reflective surface is d.
- 5) Crosstalk (I_{CX}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (6) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.
- (7) All parameters tested using pulse techniques.

OPB703, OPB703WZ

OPB704, OPB704WZ

OPB705, OPB705WZ

OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

 $V_{CE} = 5 \text{ V}, I_F = 40 \text{mA}^{(6)}$



 $V_{CE} = 5 \text{ V}, I_F = 40 \text{mA}^{(4)}$

Electrical Characteristics (T_A = 25° C unless otherwise noted) **(OPB70AWZ)**

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS			
Input Diode (See OP265 for additional information — for reference only)									
V _F	Forward Voltage	1	-	1.7	V	I _F = 40mA			
I _R	Reverse Current	1	-	100	μA	$V_R = 2 V$			
Output PhotoDarlington (See OP535 for additional information — for reference only)									
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	15	-	-	V	I _{CE} = 1.0 mA, E _E =0			
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5	-	-	V	$I_{EC} = 100 \mu A, E_E = 0$			
I _{CEO}	Collector Dark Current	-	-	250	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$			
Coupled									
I _{C(ON)}	On-State Collector Current	5.0	ı	26.0	mA	V_{CE} = 5 V, I_F = 40mA , d = 0.15" $^{(2)(5)}$			
V _(SAT)	Saturation Voltage		-	1.15	V	I_{C} = 400 $\mu A,~I_{F}$ = 40mA , d = 0.15" $^{(2)(5)}$			
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Notes:

 I_{CX}

Crosstalk

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.82 mW/° C above 25° C.
- (3) The distance from the assembly face to the reflective surface is d.
- (4) Crosstalk (I_{cx}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (5) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.
- (6) All parameters tested using pulse techniques.



Electrical Characteristics (T_A = 25° C unless otherwise noted) **(OPB70BWZ)**

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS				
Input Diode (See OP265 for additional information — for reference only)										
V_{F}	Forward Voltage	-	-	1.7	V	I _F = 40mA				
I _R	Reverse Current	-	-	100	μA	V _R = 2 V				
Output Pho	Output Phototransistor (See OP705 for additional information — for reference only)									
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _{CE} = 100 μA				
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	0.4	-	-	V	I _{EC} = 100μA				
I _{CEO}	Collector Dark Current	-	-	100	nA	V _{CE} = 10 V, I _F = 0, E _E =0				
Coupled										
I _{C(ON)}	On-State Collector Current OPB70BWZ	0.50	-	3.0	mA	V _{CE} = 5 V, I _F = 40mA , d = 0.15" (3)(6)				
I _{cx}	Crosstalk OPB70BWZ	-	-	5	μA	V _{CE} = 5 V, I _F = 40mA ⁽⁵⁾				

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) For OPB703, OPB704 and OPB705, derate linearly 1.67 mW/° C above 25° C.
- (3) For OPB703WZ, OPB704WZ, OPB705WZ and OPB70BWZ, derate linearly 1.82 mW/° C above 25° C.
- (4) The distance from the assembly face to the reflective surface is d.
- (5) Crosstalk (I_{CX}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (6) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.
- (7) All parameters tested using pulse techniques.



Electrical Characteristics ($T_A = 25^{\circ}$ C unless otherwise noted) (OPB70CWZ and OPB70EWZ)

SYMBOL	SYMBOL PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS			
Input Diode (See OVLAS6CB8 for additional information — for reference only)									
V_{F}	Forward Voltage	ı	1	2.6	V	I _F = 40mA			
I _R	Reverse Current	Ī	ı	100	μA	V _R = 2 V			
Output Ph	ototransistor (See OP505 for additional in	nformat	ion — fo	or refere	ence only	y)			
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	1	-	V	$I_{CE} = 100 \mu A, I_F = 0, E_E = 0$			
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	0.4	ı	-	V	$I_{EC} = 100 \mu A, I_F = 0, E_E = 0$			
I _{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$			

Coupled

	On-State Collector Current	OPB70CWZ	.10	-	1.0	m Λ	V _{CE} = 5 V, I _F = 40mA , d = 0.15" (2)(5)
I _C (ON)	On-State Collector Current	OPB70EWZ	.25	ı	2.5	mA	V _{CE} = 5 V, I _F = 40IIIA , d = 0.15 \
V _(SAT)	Saturation Voltage		-	-	0.4	V	I_C = 100 μ A, I_F = 40mA , d = 0.15" $^{(2)(5)}$
I _{CX}	Crosstalk		-	-	2	μΑ	$V_{CE} = 5 \text{ V}, I_F = 40 \text{mA}^{(4)}$

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) For OPB703WZ, OPB704WZ, OPB705WZ and OPB70BWZ, derate linearly 1.82 mW/° C above 25° C.
- (3) The distance from the assembly face to the reflective surface is d.
- Lower curve is based on a calculated worst-case condition, rather than the conventional -2Ω limit.
- (5) Crosstalk (I_{CX}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (6) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.
- (7) All parameters tested using pulse techniques.



Electrical Characteristics ($T_A = 25^{\circ}$ C unless otherwise noted) **(OPB70DWZ and OPB70FWZ)**

SYMBOL	PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode (See OVLAS6CB8 for additional information — for reference only)								
V _F	Forward Voltage	-	1	2.6	V	I _F = 40mA		
I _R	Reverse Current	-	ı	100	μA	V _R = 2 V		
Output Ph	ototransistor (See OP505 for additional in	nformat	ion — fo	or refere	ence only	y)		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	1	-	V	$I_{CE} = 100 \mu A, I_F = 0, E_E = 0$		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	1	-	V	$I_{EC} = 100 \mu A, I_F = 0, E_E = 0$		
I _{CEO}	Collector Dark Current	-	-	250	nA	V _{CE} = 10 V, I _F = 0, E _E =0		

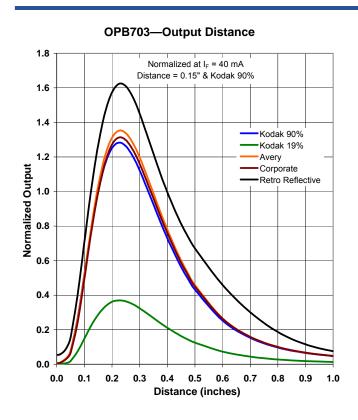
Coupled

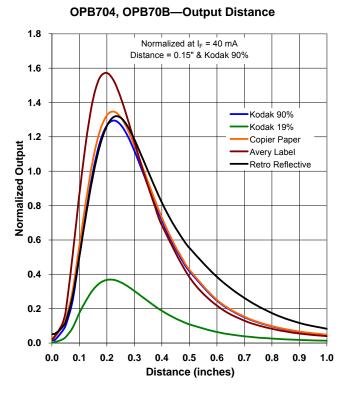
	On-State Collector Current	OPB70DWZ	.10	-	1.5	m Λ	V _{CE} = 5 V, I _F = 40mA , d = 0.15" ⁽²⁾⁽⁵⁾
I _{C(ON)}	On-State Collector Current	OPB70FWZ	.25	ı	3.5	mA	V _{CE} = 5 V, I _F = 40IIIA , U = 0.15 ***
V _(SAT)	Saturation Voltage		-	-	0.4	V	$I_{C(ON)}$ = 100 μ A, I_F = 40mA , d = 0.15" (2)(5)
I _{CX}	Crosstalk		-	-	5.0	μΑ	V _{CE} = 5 V, I _F = 40mA ⁽⁴⁾

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) For OPB703WZ, OPB704WZ, OPB705WZ and OPB70BWZ, derate linearly 1.82 mW/° C above 25° C.
- (3) The distance from the assembly face to the reflective surface is d.
- (4) Crosstalk (I_{CX}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (5) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.
- (6) All parameters tested using pulse techniques.







OPB705, OPB70A, OPB70C, OPB70D—Output Distance

